



**FIG. 1**



01-125/1C

REPLACEMENT SHEET

2 / 2

PROVIDING AN INTEGRATED CIRCUIT  
STRUCTURE HAVING A LAYER OF LOW K  
CARBON-DOPED SILICON OXIDE DIELECTRIC  
MATERIAL THEREON WITH VIAS ETCHED  
THROUGH THE LAYER OF LOW K DIELECTRIC  
MATERIAL USING A PHOTORESIST MASK OVER  
THE LAYER OF LOW K DIELECTRIC MATERIAL

EXPOSING THE INTEGRATED CIRCUIT  
STRUCTURE TO A PLASMA FORMED FROM ONE  
OR MORE REDUCING AGENTS TO REMOVE AT  
LEAST SOME OF THE RESIST MASK AND AT  
LEAST SOME OF THE ETCH RESIDUES

EXPOSING THE INTEGRATED CIRCUIT  
STRUCTURE TO A DIRECTIONAL BEAM OF  
CHARGED PARTICLES FROM A PLASMA  
FORMED FROM ONE OR MORE OXIDIZING  
AGENTS TO REMOVE ANY REMAINING ETCH  
RESIDUES FROM BOTH FORMATION OF THE  
VIAS AND REMOVAL OF THE RESIST MASK

**FIG. 2**